

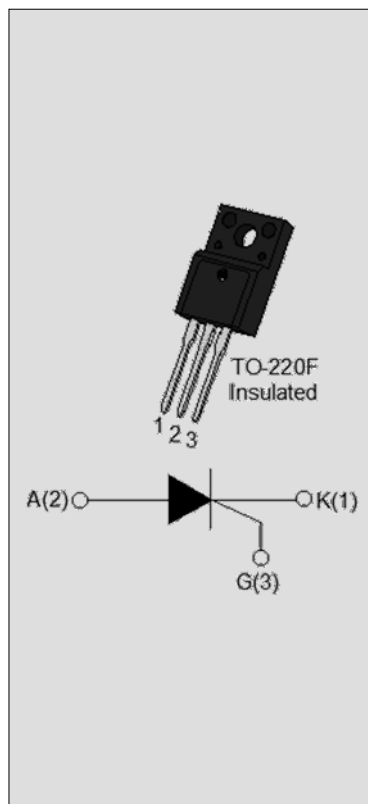


JCT610F 10A SCR

Rev.A.1.1

^ Z / W d / K E W

With high ability to withstand the shock loading of large current, JCT610F of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT610F provides a rated insulation voltage of 2000 V_{RMS} , complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



D / E & dhZ ^

Symbol	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	10	mA

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Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c 085^\circ C$)	$I_{T(AV)}$	6.5	A
RMS on-state current ($T_c 085^\circ C$)	$I_{T(RMS)}$	10	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	110	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		120	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	61	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	100	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.7	kV

$> dZ / >$, $Z d Z / >$ (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L$ (T				

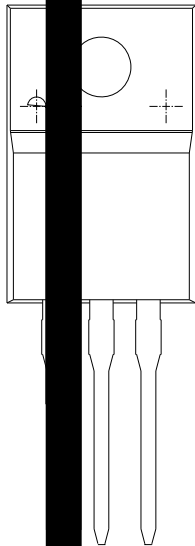
JCT610F

 JieJie Microelectronics Co., Ltd.

KZ Z/E' E & KZD d/KE

J	CT	6	10	F
JieJie Microelectronics Co., Ltd.	SCRs			F:TO-220F(Ins)
6:VDRM/VRRM 1600V			IT(RMS):10A	

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FIG.1: Maximum power dissipation versus RMS on-state current

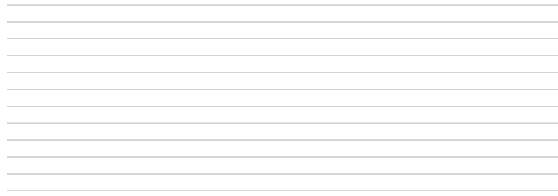
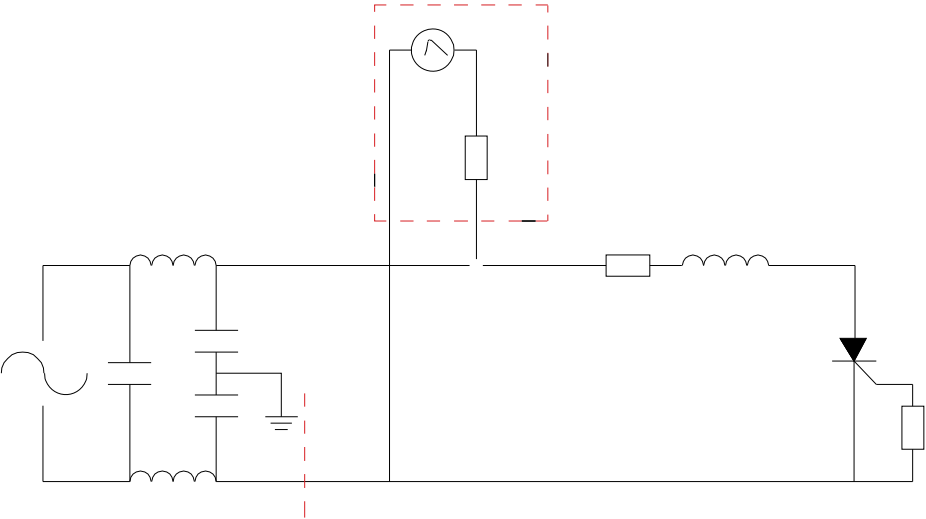


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.





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Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT610F	600	10	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Sept.28, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA


JCT610F

 **JieJie Microelectronics Co., Ltd.**

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